



1N60

Power MOSFET

1.2A, 600V N-CHANNEL POWER MOSFET

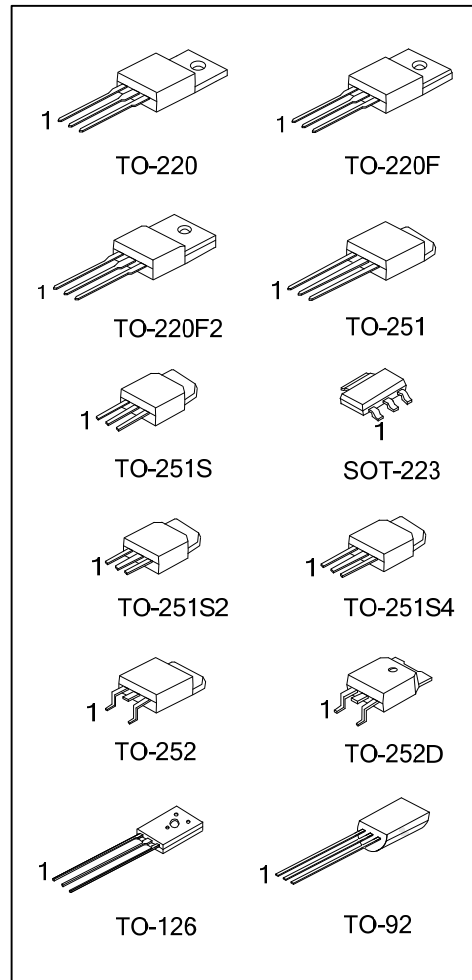
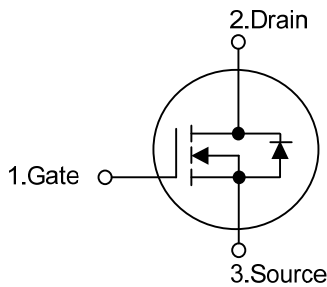
DESCRIPTION

The UTC 1N60 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 11.5\Omega @ V_{GS}=10V, I_D=0.6A$
- * Ultra Low gate charge (typical 5.0nC)
- * Low reverse transfer capacitance (C_{RSS} = typical 3.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	1N60G-AA3-R	SOT-223	G	D	S	Tape Reel
1N60L-TA3-T	1N60G-TA3-T	TO-220	G	D	S	Tube
1N60L-TF2-T	1N60G-TF2-T	TO-220F2	G	D	S	Tube
1N60L-TF3-T	1N60G-TF3-T	TO-220F	G	D	S	Tube
1N60L-TM3-T	1N60G-TM3-T	TO-251	G	D	S	Tube
1N60L-TMS-T	1N60G-TMS-T	TO-251S	G	D	S	Tube
1N60L-TMS2-T	1N60G-TMS2-T	TO-251S2	G	D	S	Tube
1N60L-TMS4-T	1N60G-TMS4-T	TO-251S4	G	D	S	Tube
1N60L-TN3-R	1N60G-TN3-R	TO-252	G	D	S	Tape Reel
1N60L-TND-R	1N60G-TND-R	TO-252D	G	D	S	Tape Reel
1N60L-T60-K	1N60G-T60-K	TO-126	G	D	S	Bulk
1N60L-T92-B	1N60G-T92-B	TO-92	G	D	S	Tape Box
1N60L-T92-K	1N60G-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N60G-AA3-R</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk, T: Tube, R: Tape Reel</p> <p>(2) AA3: SOT-223, T92: TO-92, TA3: TO-220, TF2: TO-220F2, TF3: TO-220F, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TND: TO-252D, T60: TO-126</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING

PACKAGE	MARKING
SOT-223	<p>1N60G</p> <p>1 → Data Code</p>
TO-220 TO-220F TO-220F2 TO-251 TO-251S TO-251S2 TO-251S4 TO-252 TO-252D	<p>UTC 1N60</p> <p>Lot Code ← → Data Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free</p>
TO-126	<p>UTC 1N60</p> <p>→ Data Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free</p>
TO-92	<p>UTC 1N60</p> <p>→ Data Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free</p>

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	1.2	A
Continuous Drain Current		I_D	1.2	A
Pulsed Drain Current (Note 2)		I_{DM}	4.8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	50	mJ
	Repetitive (Note 2)	E_{AR}	4.0	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	SOT-223	P_D	8	W
	TO-251/TO-252 TO-252D/TO-251S TO-251S2/ TO-251S4		28	
	TO-220		40	
	TO-220F		21	
	TO-220F2		23	
	TO-92($T_A=25^\circ\text{C}$)		1	
	TO-126		12.5	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 60\text{mH}$, $I_{AS} = 1\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 1.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

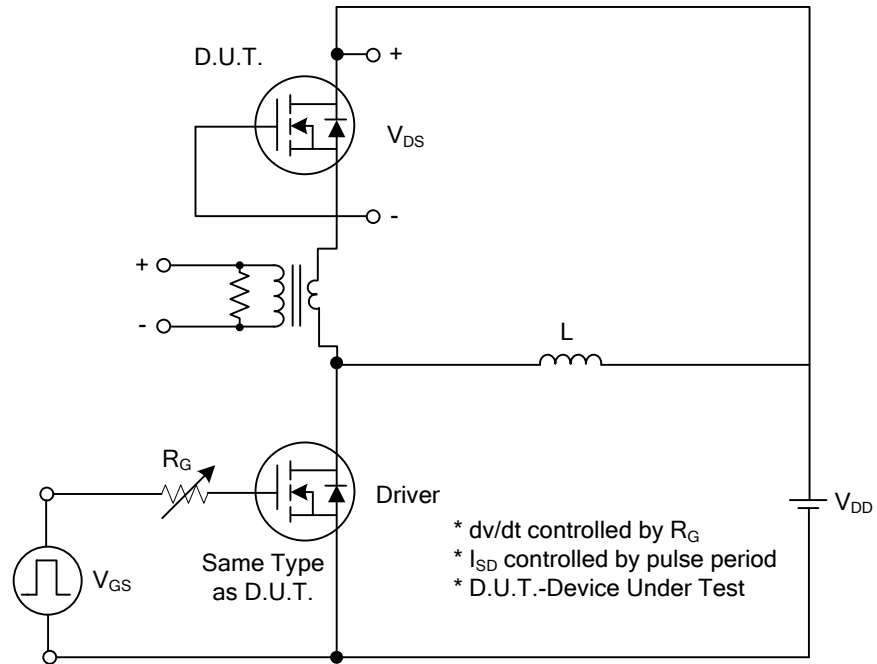
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-251/TO-252 TO-252D/TO-251S TO-251S2/ TO-251S4		110	
	TO-220/TO-220F		62.5	
	TO-220F2		62.5	
	TO-92		140	
	TO-126		132	
	Junction to Case		SOT-223	
TO-251/TO-252 TO-252D/TO-251S TO-251S2/ TO-251S4		4.53		
TO-220		3.13		
TO-220F		5.95		
TO-220F2		5.43		
TO-92		80		
TO-126		10		

■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified.)

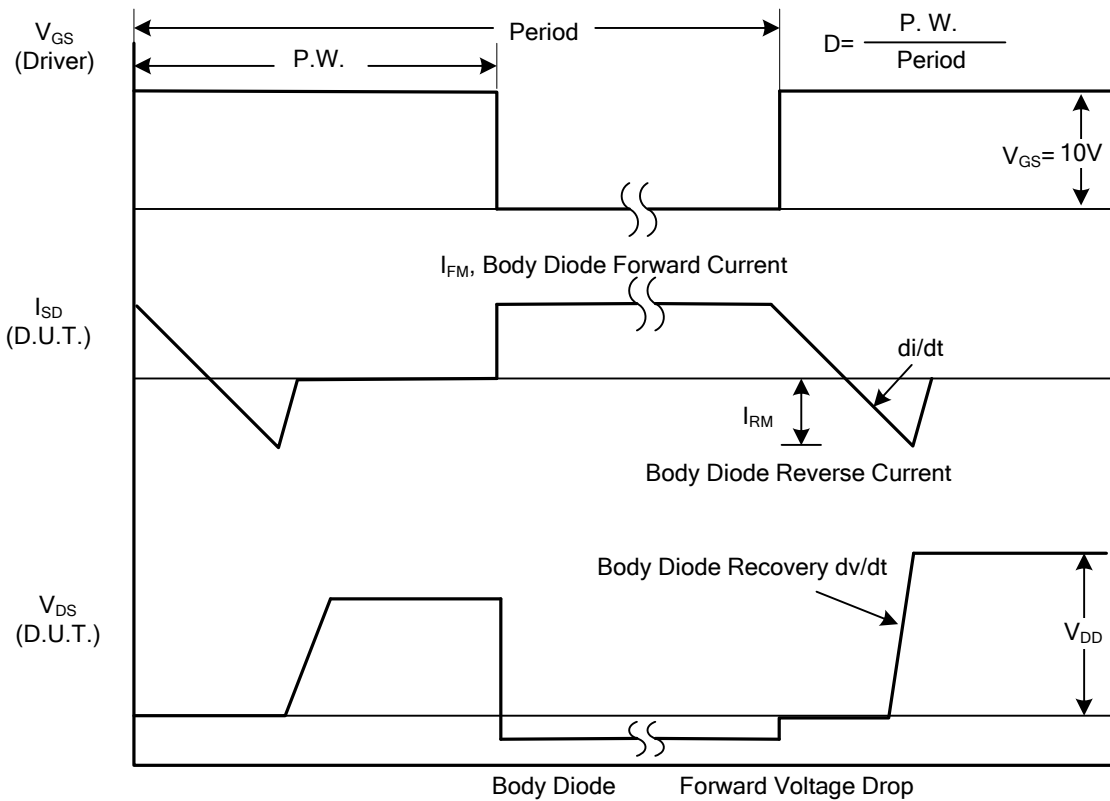
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$		0.4		$V/^\circ C$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.6A$		9.3	11.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		120	150	pF
Output Capacitance	C_{OSS}			20	25	pF
Reverse Transfer Capacitance	C_{RSS}			3.0	4.0	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=300V, I_D=1.2A, R_G=50\Omega$ (Note 2,3)		5	20	ns
Turn-On Rise Time	t_R			25	60	ns
Turn-Off Delay Time	$t_{D(OFF)}$			7	25	ns
Turn-Off Fall Time	t_F			25	60	ns
Total Gate Charge	Q_G	$V_{DS}=480V, V_{GS}=10V, I_D=1.2A$ (Note 2,3)		5.0	6.0	nC
Gate-Source Charge	Q_{GS}			1.0		nC
Gate-Drain Charge	Q_{GD}			2.6		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.2A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				1.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				4.8	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=1.2A$		160		ns
Reverse Recovery Charge	Q_{RR}	$dI_F/dt=100A/\mu s$ (Note 1)		0.3		μC

- Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature
 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
 3. Essentially Independent of Operating Temperature

■ TEST CIRCUITS AND WAVEFORMS

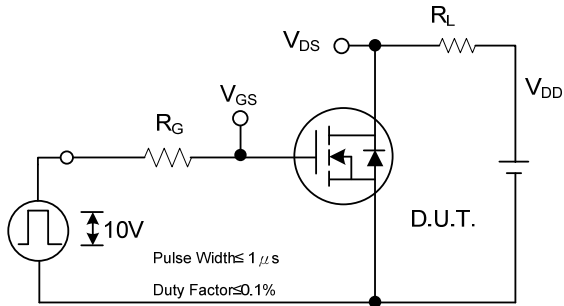


Peak Diode Recovery dv/dt Test Circuit

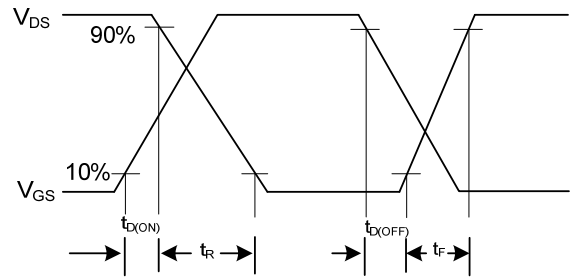


Peak Diode Recovery dv/dt Waveforms

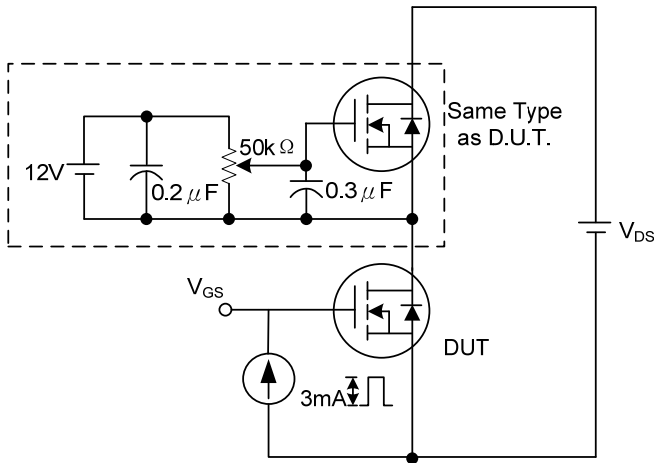
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



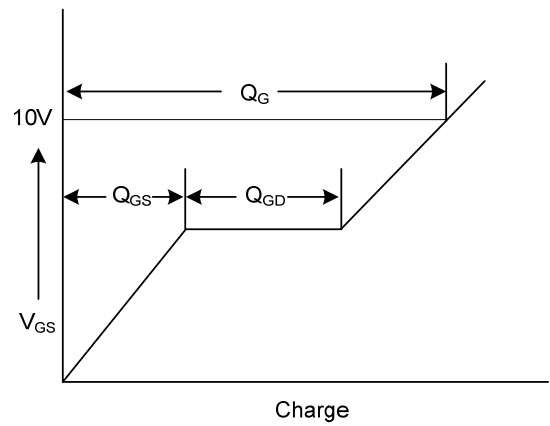
Switching Test Circuit



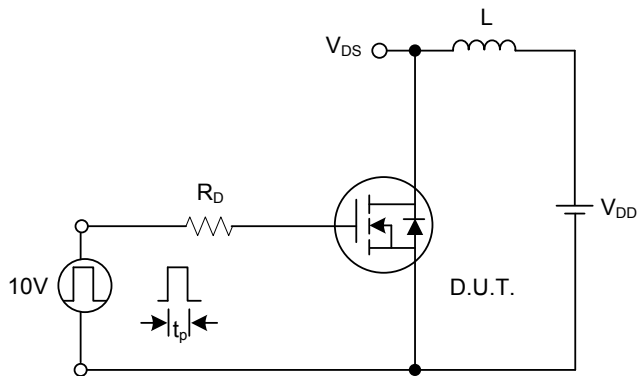
Switching Waveforms



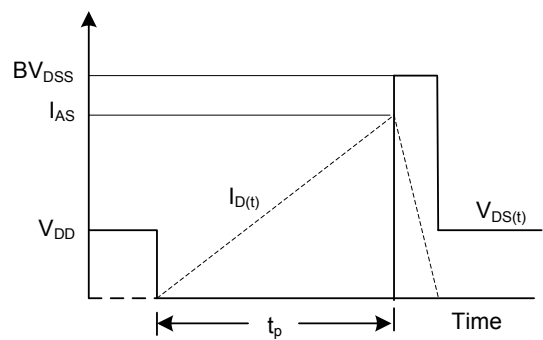
Gate Charge Test Circuit



Gate Charge Waveform

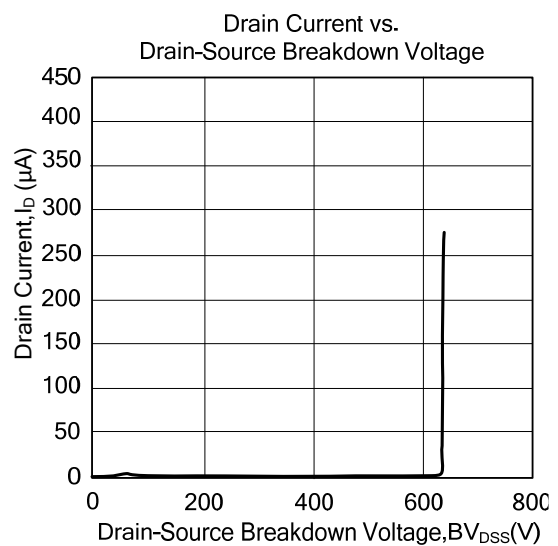
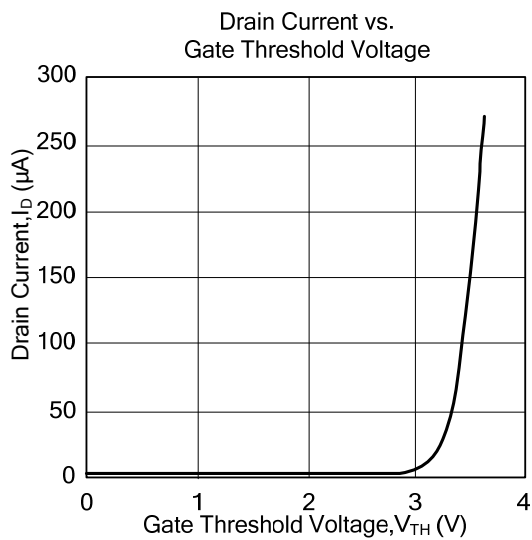
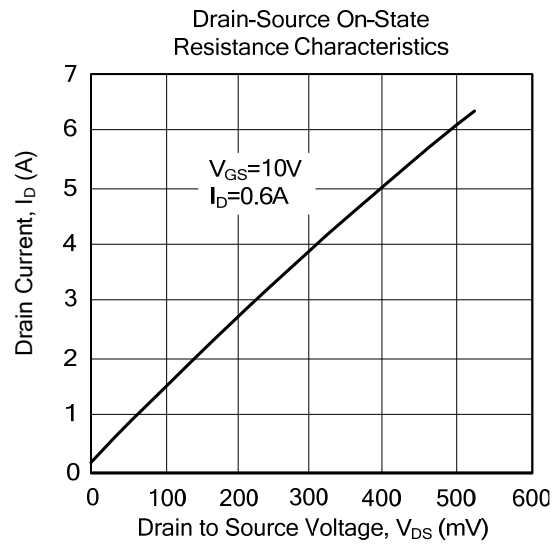
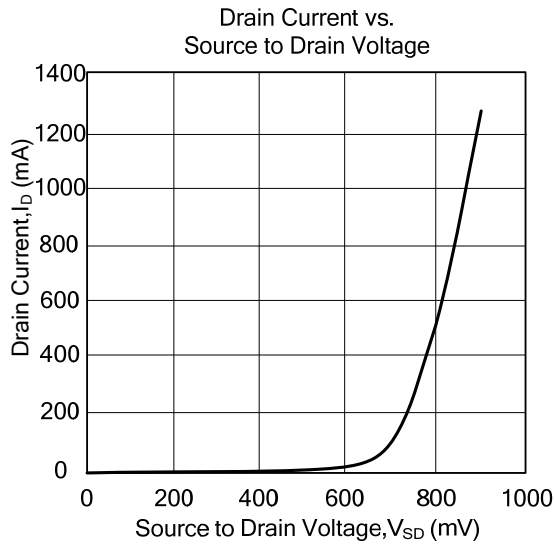


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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